Takuya Kawazu

List of Publications by Year
in descending order

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35	228	1307594	1058476
papers	citations	7	14
		h-index	g-index

36	36	36	195
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Synchronously wired infrared antennas for resonant single-quantum-well photodetection up to room temperature. Nature Communications, 2020, 11, 565.	12.8	40
2	Optical properties of GaSb/GaAs type-Ð†Ð† quantum dots grown by droplet epitaxy. Applied Physics Letters, 2009, 94, 081911.	3.3	37
3	Effects of Sb/As intermixing on optical properties of GaSb type-II quantum dots in GaAs grown by droplet epitaxy. Applied Physics Letters, 2010, 97, 261906.	3.3	22
4	Growth of GaSb dots on GaAs(100) by droplet epitaxy. Physica Status Solidi (B): Basic Research, 2009, 246, 733-735.	1.5	16
5	Self-assembly of InAs ring complexes on InP substrates by droplet epitaxy. Journal of Applied Physics, 2012, 112, 063510.	2.5	14
6	Near-field resonant photon sorting applied: dual-band metasurface quantum well infrared photodetectors for gas sensing. Nanophotonics, 2020, 9, 4775-4784.	6.0	13
7	Systematic studies for improving device performance of quantum well infrared stripe photodetectors. Nanophotonics, 2020, 9, 3373-3384.	6.0	10
8	Growth of GaSb quantum dots on GaAs (311)A. Journal of Crystal Growth, 2013, 378, 475-479.	1.5	7
9	EFFECTS OF ANTIMONY FLUX ON MORPHOLOGY AND PHOTOLUMINESCENCE SPECTRA OF GaSb QUANTUM DOTS FORMED ON GaAs BY DROPLET EPITAXY. Journal of Nonlinear Optical Physics and Materials, 2010, 19, 819-826.	1.8	6
10	Effects of Interface Grading on Electronic States and Optical Transitions in GaSb Type-II Quantum Dots in GaAs. Japanese Journal of Applied Physics, 2011, 50, 04DJ06.	1.5	6
11	Optical anisotropy of GaSb type-II nanorods on vicinal (111)B GaAs. Applied Physics Letters, 2011, 99, 231901.	3.3	5
12	Optical AND operation in n-AlGaAs/GaAs heterojunction field effect transistor. Applied Physics Letters, 2018, 112, .	3.3	5
13	Growth of GaSb and InSb quantum dots on GaAs (311)A by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 275-277.	0.8	4
14	Electric states in laterally and vertically arrayed type-II quantum dots. Japanese Journal of Applied Physics, 2015, 54, 04DJ01.	1.5	4
15	Lateral current generation in n-AlGaAs/GaAs heterojunction channels by Schottky-barrier gate illumination. Applied Physics Letters, 2015, 106, 022103.	3.3	4
16	Effects of Interface Grading on Electronic States and Optical Transitions in GaSb Type-II Quantum Dots in GaAs. Japanese Journal of Applied Physics, 2011, 50, 04DJ06.	1.5	4
17	Electron scatterings in selectively doped n-AlGaAsâˆ•GaAs heterojunctions with high density self-assembled InAlAs antidots. Applied Physics Letters, 2008, 93, 132116.	3.3	3
18	Effects of interface grading on optical anisotropy in type-II quantum wells on high-index substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1351-1356.	2.7	3

#	Article	IF	Citations
19	Postâ€growth annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1505-1508.	0.8	3
20	GaAs/AlGaAs quantum wells with indirect-gap AlGaAs barriers for solar cell applications. Applied Physics Letters, 2014, 104, .	3.3	3
21	Photoinduced current in n-AlGaAs/GaAs heterojunction field-effect transistor driven by local illumination in edge regions of Schottky metal gate. Japanese Journal of Applied Physics, 2017, 56, 04CG04.	1.5	3
22	Valence Band Mixing in GaAs/AlGaAs Quantum Wells Adjacent to Self-Assembled InAlAs Antidots. Journal of Nanomaterials, 2019, 2019, 1-7.	2.7	3
23	Thermal annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2742-2744.	2.7	2
24	Anisotropic Transport of Electrons in a Novel FET Channel with Chains of InGaAs Nano-Islands Embedded along Quasi-Periodic Multi-Atomic Steps on Vicinal (111)B GaAs. , 2010, , .		2
25	Photo-induced current in n-AlGaAs/GaAs heterojunction channels driven by local illumination at the edge regions of Hall bar. Applied Physics Letters, 2013, 102, 252104.	3.3	2
26	Optical anisotropy of InGaAs quantum wire arrays on vicinal (111)B GaAs. Journal of Applied Physics, 2016, 120, 134309.	2.5	2
27	Excitation power dependence of photoluminescence spectra of GaSb type-II quantum dots in GaAs grown by droplet epitaxy. AIP Advances, 2016, 6, 045312.	1.3	2
28	Optical anisotropy of InGaAs quantum dot arrays aligned along multiatomic steps on vicinal GaAs(111)B. Journal of Applied Physics, 2017, 122, 204304.	2.5	1
29	Effects of Interface Grading on Electronic States in Columnar Type-II Quantum Dots. Japanese Journal of Applied Physics, 2012, 51, 02BJ09.	1.5	1
30	Metasurface Quantum Well Photodetectors with Broadened Photoresponse Using a Patchwork of Cavities within a Subwavelength Period. , 2020, , .		1
31	Magneto-capacitance study of an n-AlGaAs/GaAs heterojunction supporting a sizable dc current. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2879-2881.	0.8	0
32	Effects of Ga deposition rate and Sb flux on morphology of GaSb quantum dots formed on GaAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 14, 1600109.	0.8	0
33	Temperature dependence of Schottky photocurrent for local gate edge illumination in n-AlGaAs/GaAs/AlGaAs double-heterojunction field-effect transistor. Japanese Journal of Applied Physics, 2019, 58, SIIB05.	1.5	0
34	Growth of GaSb quantum dots on GaAs (111)A. E-Journal of Surface Science and Nanotechnology, 2014, 12, 304-306.	0.4	0
35	Enhancement of infrared photo-responses of the Schottky gate region of an n-AlGaAs/GaAs heterojunction FET by a second light illumination. Japanese Journal of Applied Physics, 2020, 59, 124003.	1.5	0